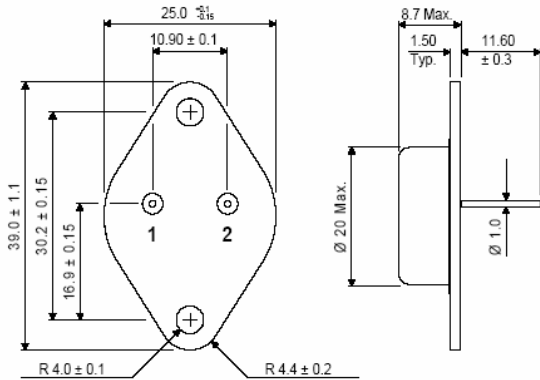


**MECHANICAL DATA**  
Dimensions in mm



**TO-3**

Pin 1 – Gate

Pin 2 – Drain

Case – Source

## N-CHANNEL POWER MOSFET

### POWER MOSFETS FOR AUDIO APPLICATIONS

**FEATURES**

- HIGH SPEED SWITCHING
- N-CHANNEL POWER MOSFET
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (160V & 200V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODE
- P-CHANNEL ALSO AVAILABLE AS BUZ905 & BUZ906

**ABSOLUTE MAXIMUM RATINGS**

( $T_{case} = 25^{\circ}C$  unless otherwise stated)

		BUZ900	BUZ901
$V_{DSX}$	Drain – Source Voltage	160V	200V
$V_{GSS}$	Gate – Source Voltage	$\pm 14V$	
$I_D$	Continuous Drain Current	8A	
$I_{D(PK)}$	Body Drain Diode	8A	
$P_D$	Total Power Dissipation @ $T_{case} = 25^{\circ}C$	125W	
$T_{stg}$	Storage Temperature Range	$-55$ to $150^{\circ}C$	
$T_j$	Maximum Operating Junction Temperature	$150^{\circ}C$	
$R_{\theta JC}$	Thermal Resistance Junction – Case	$1^{\circ}C/W$	

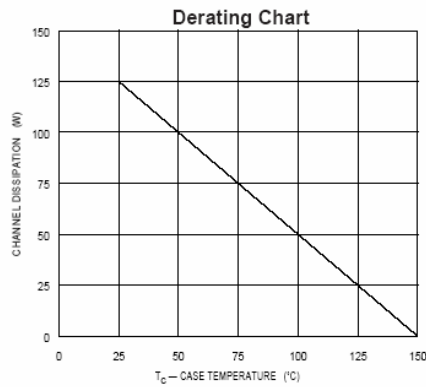
**STATIC CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

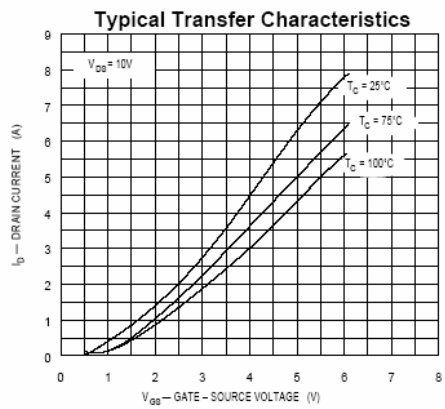
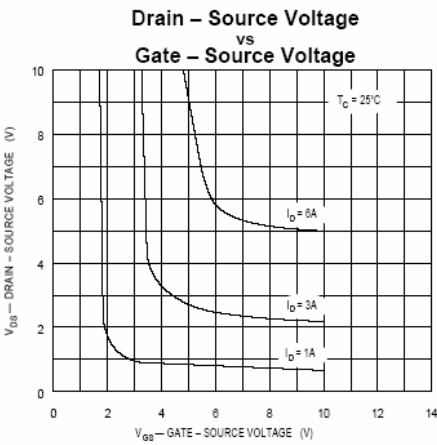
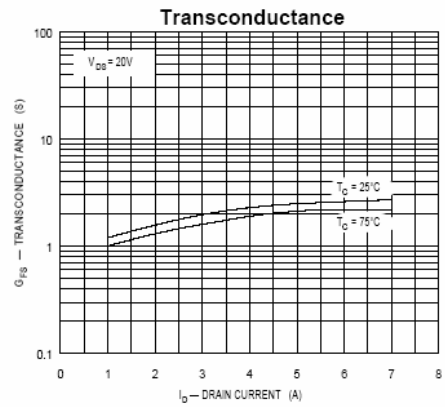
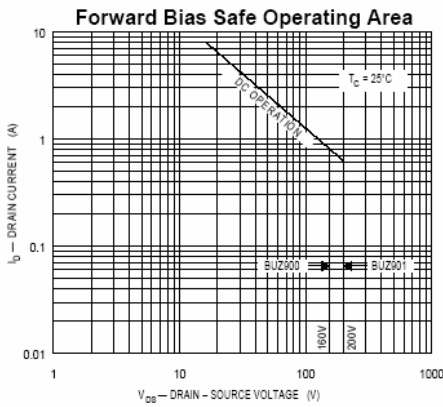
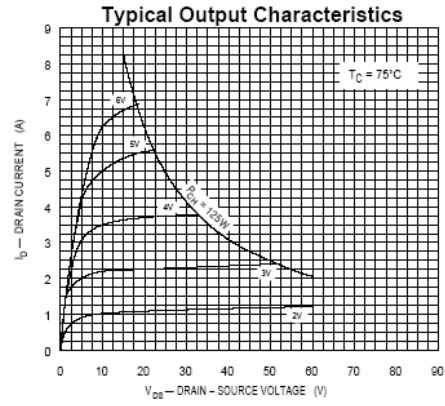
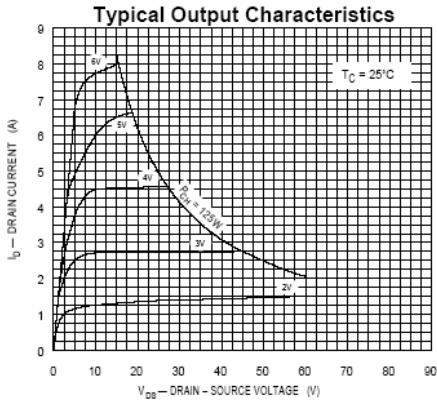
Characteristic		Test Conditions		Min.	Typ.	Max.	Unit
BV <sub>DSX</sub>	Drain – Source Breakdown Voltage	V <sub>GS</sub> = -10V	BUZ900	160			V
		I <sub>D</sub> = 10mA	BUZ901	200			
BV <sub>GSS</sub>	Gate – Source Breakdown Voltage	V <sub>DS</sub> = 0	I <sub>G</sub> = ±100μA	±14			V
V <sub>GS(OFF)</sub>	Gate – Source Cut-Off Voltage	V <sub>DS</sub> = 10V	I <sub>D</sub> = 100mA	0.15		1.5	V
V <sub>DS(SAT)*</sub>	Drain – Source Saturation Voltage	V <sub>GD</sub> = 0	I <sub>D</sub> = 8A			12	V
I <sub>DSX</sub>	Drain – Source Cut-Off Current	V <sub>GS</sub> = -10V	V <sub>DS</sub> = 160V BUZ900			10	mA
			V <sub>DS</sub> = 200V BUZ901			10	
yfs*	Forward Transfer Admittance	V <sub>DS</sub> = 10V	I <sub>D</sub> = 3A	0.7		2	S

**DYNAMIC CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

Characteristic		Test Conditions		Min.	Typ.	Max.	Unit
C <sub>iSS</sub>	Input Capacitance	V <sub>DS</sub> = 10V f = 1MHz			500		pF
C <sub>oSS</sub>	Output Capacitance				300		
C <sub>rSS</sub>	Reverse Transfer Capacitance				10		
t <sub>on</sub>	Turn-on Time	V <sub>DS</sub> = 20V			100		ns
t <sub>off</sub>	Turn-off Time	I <sub>D</sub> = 5A			50		

\* Pulse Test: Pulse Width = 300μs , Duty Cycle ≤ 2%.







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